

**TECHNICAL DATA**  
**DATA SHEET 817, REV -**

**HERMETIC POWER MOSFET**  
**P-CHANNEL**

**FEATURES:**

- -60 Volt, 0.4 Ohm, -18 A MOSFET
- Isolated Hermetic Metal Package
- Fast Switching
- Low  $R_{DS(on)}$

**MAXIMUM RATINGS**

ALL RATINGS ARE AT  $T_C = 25^\circ\text{C}$  UNLESS OTHERWISE SPECIFIED.

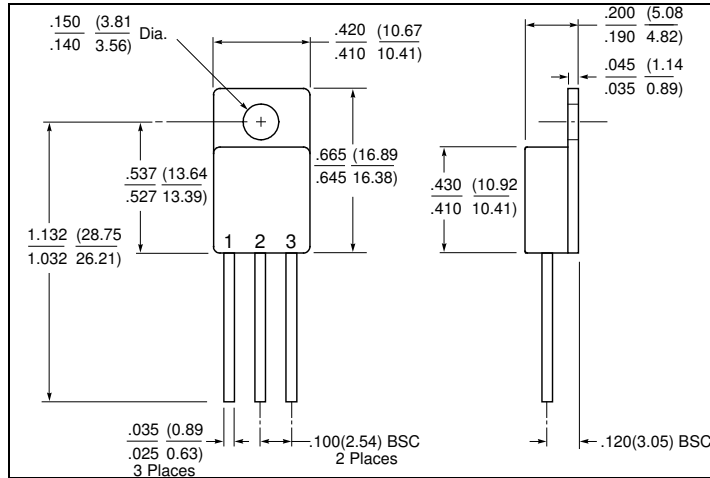
RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	$V_{GS}$	-	-	$\pm 20$	Volts
ON-STATE DRAIN CURRENT @ $T_C = 25^\circ\text{C}$	$I_{D(on)}$	-	-	-18	Amps
PULSED DRAIN CURRENT @ $T_C = 25^\circ\text{C}$	$I_{DM}$	-	-	-72	Amps
OPERATING AND STORAGE TEMPERATURE	$T_{OP}/T_{STG}$	-55	-	+175	$^\circ\text{C}$
THERMAL RESISTANCE, JUNCTION TO CASE	$R_{\theta JC}$	-	-	1.32	$^\circ\text{C}/\text{W}$
TOTAL DEVICE DISSIPATION @ $T_C = 25^\circ\text{C}$	$P_D$	-	-	110	Watts

**ELECTRICAL CHARACTERISTICS**

DRAIN TO SOURCE BREAKDOWN VOLTAGE $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	$BV_{DSS}$	-60	-	-	Volts
STATIC DRAIN TO SOURCE ON STATE RESISTANCE $V_{GS} = -10\text{V}, I_D = -11\text{A}$	$R_{DS(ON)}$	-	-	0.14	$\Omega$
GATE THRESHOLD VOLTAGE $V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	$V_{GS(th)}$	-2.0	-	-4.0	Volts
FORWARD TRANSCONDUCTANCE $V_{DS} = -25V_{DS(on)}, I_D = -11\text{A}$	$g_{fs}$	5.9	-	-	S(1/ $\Omega$ )
ZERO GATE VOLTAGE DRAIN CURRENT $V_{DS} = -60, V_{GS} = 0\text{V}$ $V_{DS} = -48, V_{GS} = 0\text{V}, T_J = 150^\circ\text{C}$	$I_{DSS}$	-	-	-100 -500	$\mu\text{A}$
GATE TO SOURCE LEAKAGE FORWARD $V_{GS} = 20\text{V}$ GATE TO SOURCE LEAKAGE REVERSE $V_{GS} = -20\text{V}$	$I_{GSS}$	-	-	100 -100	nA
TURN ON DELAY TIME RISE TIME TURN OFF DELAY TIME FALL TIME $V_{DD} = -30\text{V}, I_D = -18\text{A}, R_G = 12\Omega, V_{GS} = -10\text{V}$	$t_{d(ON)}$ $t_r$ $t_{d(OFF)}$ $t_f$	-	18 120 20 58	-	nsec
TOTAL GATE CHARGE $V_{GS} = -10\text{V}, I_D = -18\text{A}, V_{DS} = -48$	$Q_g$	-	-	34	nC
GATE TO SOURCE ON-STATE VOLTAGE $V_{GS} = -10\text{V}, I_D = -18\text{A}, V_{DS} = -48$	$Q_{gs}$	-	-	9.9	nC
GATE DRAIN CHARGE $V_{GS} = -10\text{V}, I_D = -18\text{A}, V_{DS} = -48$	$Q_{gd}$	-	-	16	nC
DIODE FORWARD VOLTAGE $T_C = 25^\circ\text{C}, I_S = -18\text{A}, V_{GS} = 0\text{V}$	$V_{SD}$	-	-	-6.3	Volts
REVERSE RECOVERY TIME $T_J = 25^\circ\text{C}, I_F = -18\text{A}, di/dt = -100\text{A}/\mu\text{sec}$	$t_{rr}$	-	-	440	nsec
INPUT CAPACITANCE OUTPUT CAPACITANCE REVERSE TRANSFER CAPACITANCE $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1.0\text{MHz}$	$C_{iss}$ $C_{oss}$ $C_{rss}$	-	1100 620 100	-	pF

**SENSITRON**  
**DATA SHEET 817**  
**REVISION -**

**MECHANICAL DIMENSIONS: in Inches / mm**



**TO-257**

**PINOUT TABLE**

DEVICE TYPE	PIN 1	PIN 2	PIN 3
MOSFET TO-257 PACKAGE	DRAIN	SOURCE	GATE

**TECHNICAL DATA**

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